

DALLAS

SEMICONDUCTOR

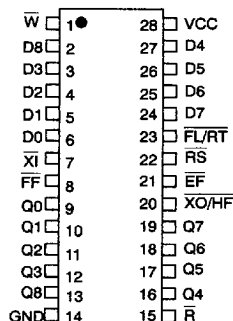
DS2013

8192 x 9 FIFO Chip

FEATURES

- First-in, first-out memory-based architecture
- Flexible 8192 x 9 organization
- Low-power HCMOS technology
- Asynchronous and simultaneous read/write
- Bidirectional applications
- Fully expandable by word width or depth
- Empty and full warning flags
- Half-full flag capability in single-device mode
- Retransmit capability
- Available in 50 ns, 65 ns, 80 ns, and 120 ns access times
- Optional industrial temperature range -40°C to +85°C available designated N

PIN ASSIGNMENT



28-Pin DIP (300 and 600 Mil)
See Mech. Drawings -- Pgs. 964 & 966

PIN DESCRIPTION

$\overline{W}$	– WRITE
$\overline{R}$	– READ
$\overline{RS}$	– RESET
$\overline{FL/RT}$	– First Load/Retransmit
D^{0-8}	– Data In
Q^{0-8}	– Data Out
$\overline{XI}$	– Expansion In
$\overline{XO/HF}$	– Expansion Out/Half Full
$\overline{FF}$	– Full Flag
$\overline{EF}$	– Empty Flag
V_{CC}	– 5 Volts
GND	– Ground
NC	– No Connect

DESCRIPTION

The DS2013 8192 x 9 FIFO Chip implements a first-in, first-out algorithm, featuring asynchronous read/write operations, full, empty, and half-full flags, and unlimited expansion capability in both word size and depth. The DS2013 is functionally and electrically equivalent to the

DS2009 512 x 9 FIFO with the exceptions listed in the notes for DC Electrical Characteristics of the DS2009 data sheet. Refer to DS2009 512 x 9 FIFO Chip data sheet for detailed device description.